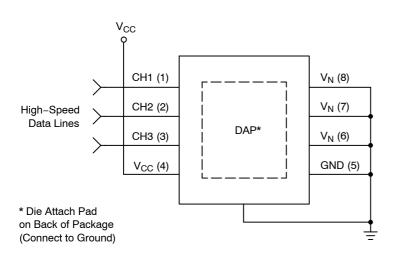
# 4-Channel Low Capacitance Dual-Voltage ESD Protection Array

#### Features

- Three Channels of Low Voltage ESD Protection
- One Channel of High Voltage ESD Protection
- Provides ESD Protection to IEC61000-4-2 Level 4:
  - ◆ ±8 kV Contact Discharge (Pins 1–3)
  - ±15 kV Contact Discharge (Pin 4)
- Low Channel Input Capacitance
- Minimal Capacitance Change with Temperature and Voltage
- High Voltage Zener Diode Protects Supply Rail
- No Need for External Bypass Capacitors
- Each I/O Pin can Withstand over 1000 ESD Strikes\*
- These Devices are Pb-Free and are RoHS Compliant



**TYPICAL APPLICATION** 

Note: All grounds must be connected.



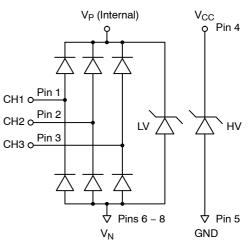
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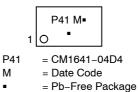
UDFN8 D4 SUFFIX CASE 517BC

**ELECTRICAL SCHEMATIC** 



Note: Pins 5 and 6 to 8 are connected to a common substrate.





(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
CM1641-04D4	UDFN-8 0.4 mm (Pb-Free)	3000/Tape & Reel

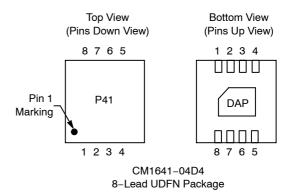
+ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

\*Standard test condition is IEC61000-4-2 level 4 test circuit with each pin subjected to ±8 kV contact discharge for 1000 pulses. Discharges are timed at 1 second intervals and all 1000 strikes are completed in one continuous test run. The part is then subjected to standard production test to verify that all of the tested parameters are within spec after the 1000 strikes.

#### Table 1. PIN DESCRIPTIONS

4–Channel, 8–Lead, UDFN–8 Package				
Pin	Name	Туре	Description	
1	CH1	I/O	LV Low-capacitance ESD Channel	
2	CH2	I/O	LV Low-capacitance ESD Channel	
3	СНЗ	I/O	LV Low-capacitance ESD Channel	
4	V <sub>CC</sub>	$HV V_{DD}$	HV ESD Channel	
5	GND	-	Ground	
6	V <sub>N</sub>	-	Negative Voltage Supply Rail	
7	V <sub>N</sub>	-	Negative Voltage Supply Rail	
8	V <sub>N</sub>	-	Negative Voltage Supply Rail	
DAP	GND	-	Die Attach Pad (Ground)	

## PACKAGE / PINOUT DIAGRAMS



# SPECIFICATIONS

#### Table 2. ABSOLUTE MAXIMUM RATINGS

Parameter	Rating	Units
DC Voltage on Low–Voltage Pins	6.0	V
DC Voltage on High-Voltage Pins (V <sub>CC</sub> pin)	14.5	V
Storage Temperature Range	–65 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

#### Table 3. STANDARD OPERATING CONDITIONS

Parameter	Rating	Units
Operating Temperature Range	-40 to +85	°C

# Table 4. ELECTRICAL OPERATING CHARACTERISTICS (Note 1)

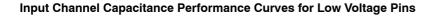
Symbol	Parameter	Conditions	Min	Тур	Max	Units
V <sub>F</sub>	LV Diode Reverse Voltage (Positive Voltage)	I <sub>F</sub> = 10 mA, T <sub>A</sub> = 25°C	6.8	8.2	9.2	V
	LV Diode Forward Voltage (Negative Voltage)	I <sub>F</sub> = 10 mA, T <sub>A</sub> = 25°C	-1.05	-0.90	-0.60	
I <sub>LEAK</sub>	LV Channel Leakage Current	$T_A = -30^\circ C$ to 65°C, $V_{IN} = 3.3 \ V$ $V_N = 0 \ V$			100	nA
C <sub>IN</sub>	LV Channel Input Capacitance	At 1 MHz, V <sub>N</sub> = 0 V, V <sub>IN</sub> = 1.65 V		1.2	1.5	pF
$\Delta C_{IN}$	LV Channel Input Capacitance Matching	At 1 MHz, V <sub>N</sub> = 0 V, V <sub>IN</sub> = 1.65 V		0.02		pF
I <sub>LEAK_HV</sub>	HV Channel Leakage Current	$T_A = 25^{\circ}C, V_{CC} = 11 \text{ V}, V_N = 0 \text{ V}$		0.1	1.0	μA
C <sub>IN_HV</sub>	HV Channel Input Capacitance	At 1 MHz, $V_N$ = 0 V, $V_{IN}$ = 2.5 V		53		pF
V <sub>F_HV</sub>	HV Diode Breakdown Voltage Positive Voltage	I <sub>F</sub> = 10 mA, T <sub>A</sub> = 25°C	14.6		17.7	V
V <sub>ESD</sub>	ESD Protection Peak Discharge Voltage at any channel input, in system Contact Discharge per IEC 61000-4-2 Standard	T <sub>A</sub> = 25°C	±8 (Pin 1–3) ±15 (Pin 4)			kV

#### Table 4. ELECTRICAL OPERATING CHARACTERISTICS (Note 1)

Symbol	Parameter	Conditions	Min	Тур	Max	Units
V <sub>CL</sub>	LV Channel Clamp Voltage (Pin 1–3) Positive Transients Negative Transients	T <sub>A</sub> = 25°C, I <sub>PP</sub> = 1 A, t <sub>P</sub> = 8/20 μS		+9.64 -1.75		V
R <sub>DYN</sub>	Dynamic Resistance LV Channel Positive Transients LV Channel Negative Transients HV Channel Positive Transients HV Channel Negative Transients	I <sub>PP</sub> = 1 A, t <sub>P</sub> = 8/20 μS Any I/O Pin to Ground		0.72 0.59 1.20 0.36		Ω

1. All parameters specified at  $T_A = -40^{\circ}C$  to  $+85^{\circ}C$  unless otherwise noted.

#### **PERFORMANCE INFORMATION**



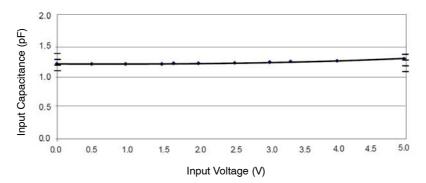
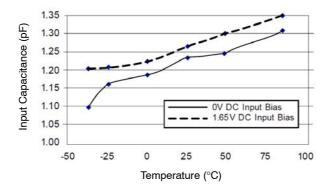
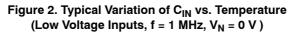


Figure 1. Typical Variation of  $C_{IN}$  vs.  $V_{IN}$ (Low Voltage Inputs, f = 1 MHz,  $V_N$  = 0 V )

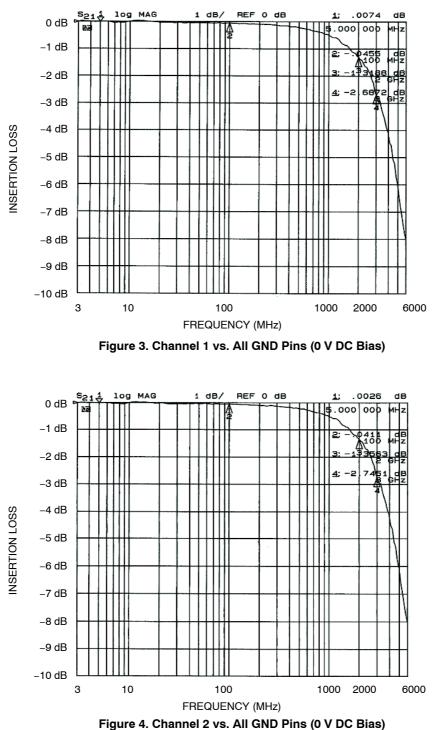




## PERFORMANCE INFORMATION (Cont'd)

# Typical Filter Performance for Low Voltage Pins

Nominal conditions unless specified otherwise, 50  $\Omega$  Environment.



# PERFORMANCE INFORMATION (Cont'd)

# Typical Filter Performance for Low Voltage Pins

Nominal conditions unless specified otherwise, 50  $\Omega$  Environment.

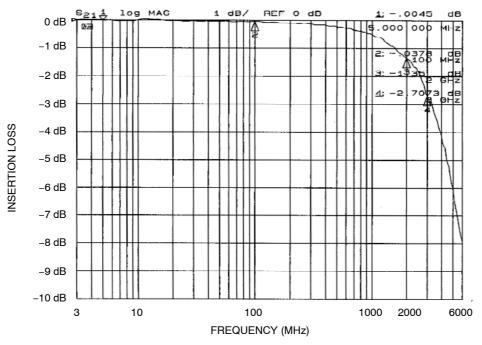


Figure 5. Channel 3 vs. All GND Pins (0 V DC Bias)

# **ONSEM**<sup>1</sup>.

	<b>UDFN8, 1.7x1.35, 0.4P</b> CASE 517BC ISSUE A		
SCALE 4:1			DATE 11 AUG 2022
2X DIDC PIN AI REFERENCE 2X DIDC TDP VIEW	ASME Y14.5M, 2. CONTROLLING 3. DIMENSION & TERMINAL AN: 0.15 AND 0.25 TIP. 4. COPLANARITY	2004, DIMENS APPLIE JIS ME MM FOR APPLIE	ASURED BETWEEN M THE TERMINAL
$\square 0.050[C]$ $\square 0.05[C]$ $\square 0$	EXPOSED Cu A1 A3	DIM A A1 A3 b	MILLIMETERS           MIN.         MAX.           0.45         0.55           0.00         0.05           0.13         REF           0.15         0.25
DETAIL A BX L BX	DETAIL A ALTERNATE CONSTRUCTIONS	D D2 E E2 e K L L1	1.70     BSC       1.10     1.30       1.35     BSC       0.30     0.50       0.40     BSC       0.15        0.20     0.30        0.05
BOTTOM VIEW	PACKAGE DUTLINE		
MARKING DIAGRAMS* $\begin{array}{c} XX M \bullet \\ \circ & \bullet \end{array}$ 1 $\begin{array}{c} XXXM \bullet \\ \circ & \bullet \end{array}$ XXX = Specific Device Code M = Date Code $\bullet = Pb$ -Free Package	<ul> <li>For additional and soldering Semiconductor</li> </ul>	RECOMI JUNTING I informatio details, pl Soldering	MENDED TOUTPRINT* n on our Pb-Free strategy ease download the DN and Mounting Techniques
(Note: Microdot may be in either location) *This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot "●", may or may not be present. Some products may not follow the Generic Marking.	Reference Mai	wat, SULUE	UNITY D

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 DESCRIPTION:
 UDFN8, 1.7x1.35, 0.4P
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